

Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
60V	85mΩ @ V _{GS} = 10V	2.5A
	120mΩ @ V _{GS} = 4.5V	2.0A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- DC-DC converters
- Power-management functions
- Backlighting

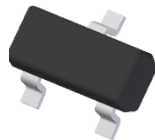
Features and Benefits

- N MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
- <https://www.diodes.com/quality/product-definitions/>
- An automotive-compliant part is available under a separate datasheet ([DMN6075SQ](#))

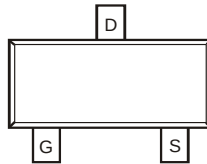
Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208③
- Weight: 0.008 grams (Approximate)

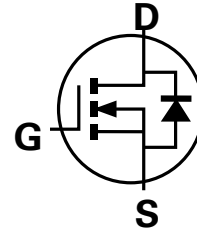
SOT23



Top View



Top View



Top View
Pin Configuration

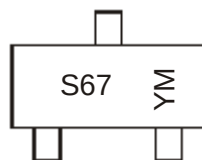
Ordering Information (Note 4)

Orderable Part Number	Package	Reel Size (inches)	Tape Width (mm)	Packing	
				Qty.	Carrier
DMN6075S-7	SOT23	7	8	3,000	Tape & Reel
DMN6075S-13	SOT23	13	8	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

SOT23



S67 = Product Type Marking Code
YM = Date Code Marking
Y or Ȳ = Year (ex: M = 2025)
M = Month (ex: 9 = September)

Date Code Key

Year	2014	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	B	-	M	N	P	R	S	T	U	V	W	X

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	2.0	A
		T _A = +70°C		1.5	
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	2.5	A
		T _A = +70°C		2.0	
Maximum Body Diode Forward Current (Note 5)			I _S	2.0	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	12	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.8	W
	T _A = +70°C		0.5	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	157	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.15	W
	T _A = +70°C		0.7	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	110	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0, I _D = 250μA
Zero Gate Voltage Drain Current, T _J = +25°C	I _{DSS}	—	—	1.0	μA	V _{DS} = 60V, V _{GS} = 0
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±16V, V _{DS} = 0
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.3	—	2.7	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	69	85	mΩ	V _{GS} = 10V, I _D = 3.2A
			75	120		V _{GS} = 4.5V, I _D = 2.8A
Diode Forward Voltage	V _{SD}	—	—	1.2	V	V _{GS} = 0, I _S = 2.5A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	606	—	pF	V _{DS} = 20V, V _{GS} = 0, f = 1.0MHz
Output Capacitance	C _{oss}	—	32.6	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	24.6	—	pF	
Gate Resistance	R _g	—	1.5	—	Ω	V _{DS} = 0, V _{GS} = 0, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	12.3	—	nC	V _{DS} = 30V, I _D = 3A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	5.6	—	nC	
Gate-Source Charge	Q _{gs}	—	1.7	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.9	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.5	—	ns	V _{GS} = 10V, V _{DS} = 30V, R _g = 20Ω, R _L = 50Ω
Turn-On Rise Time	t _r	—	4.1	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	35	—	ns	
Turn-Off Fall Time	t _f	—	11	—	ns	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

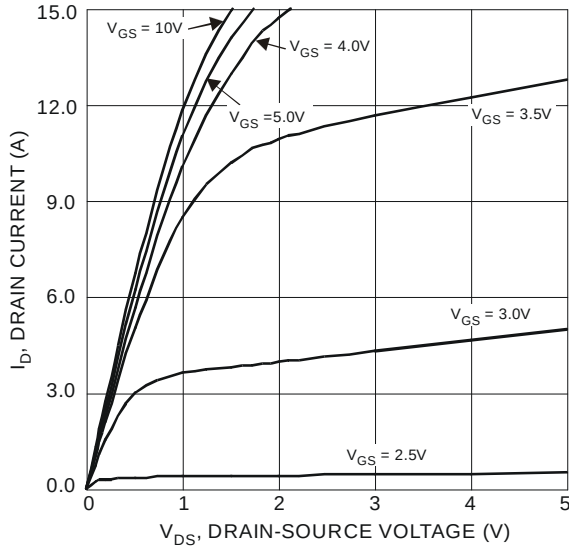


Figure 1 Typical Output Characteristics

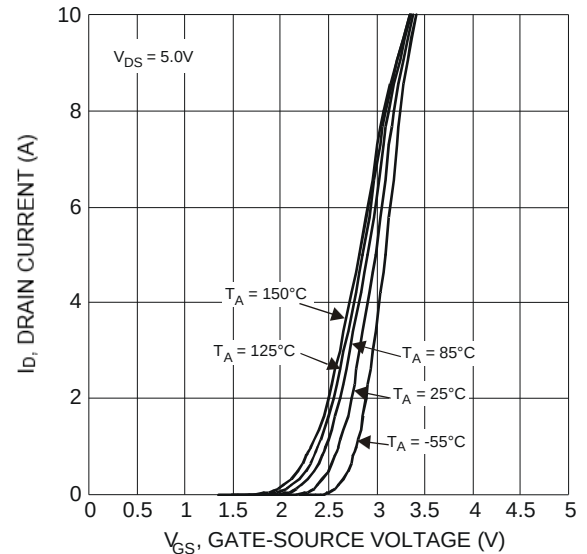


Figure 2 Typical Transfer Characteristics

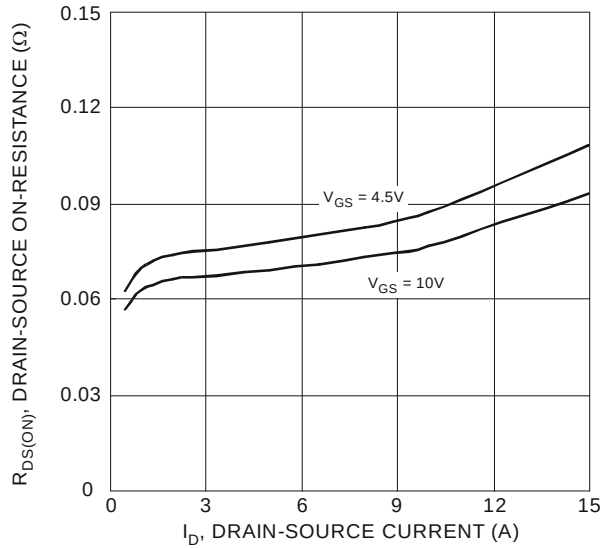


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

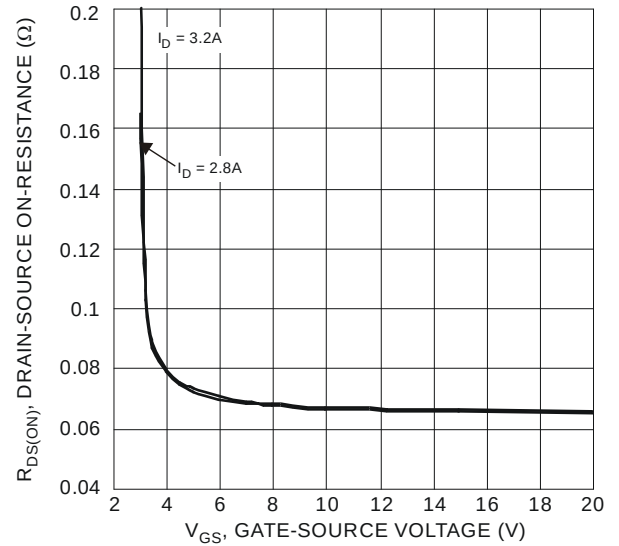


Figure 4 Typical Transfer Characteristics

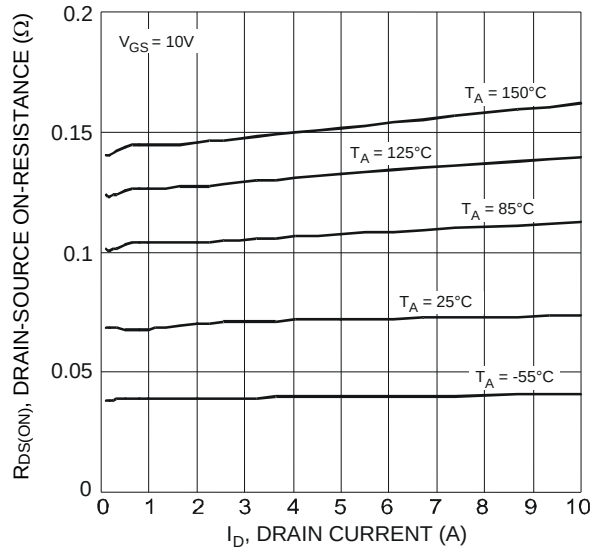


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

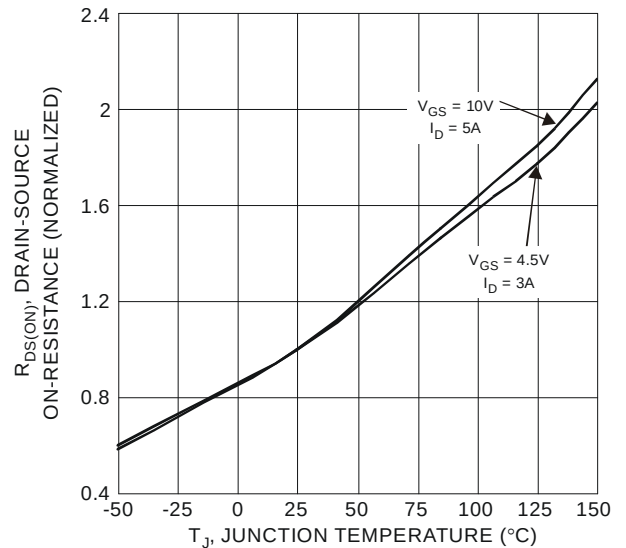
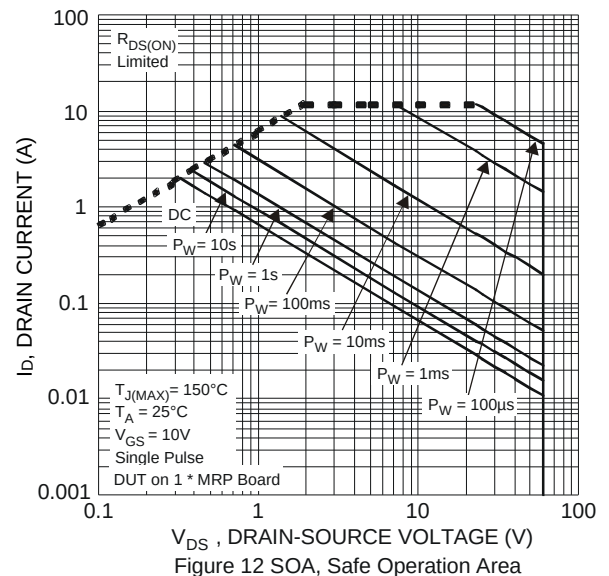
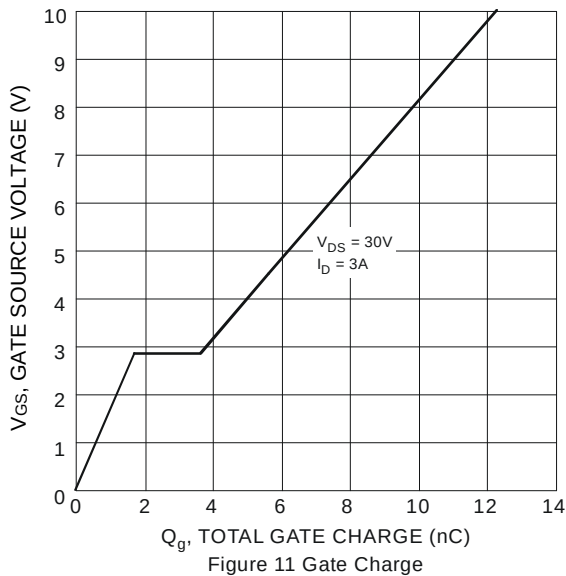
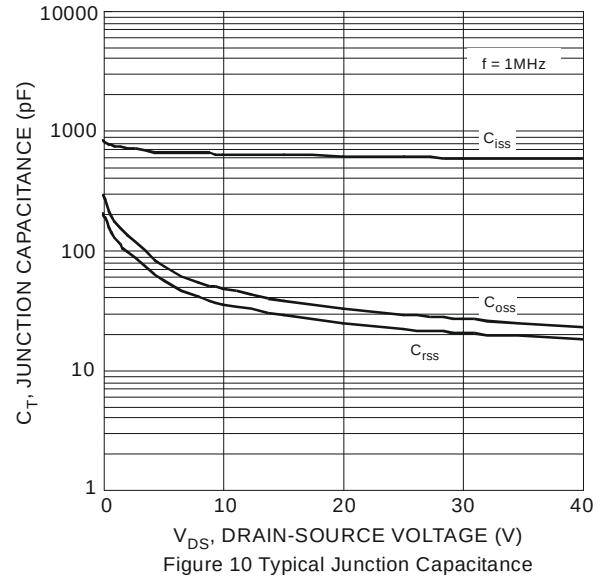
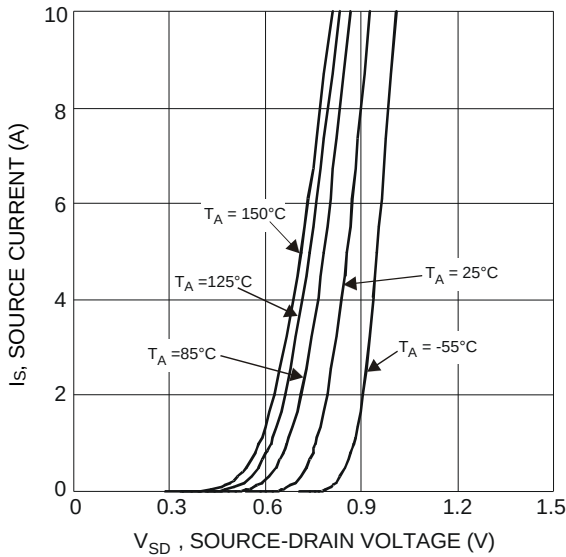
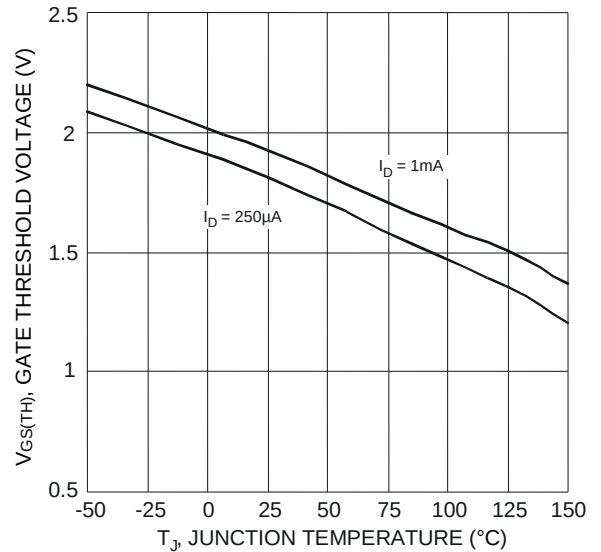
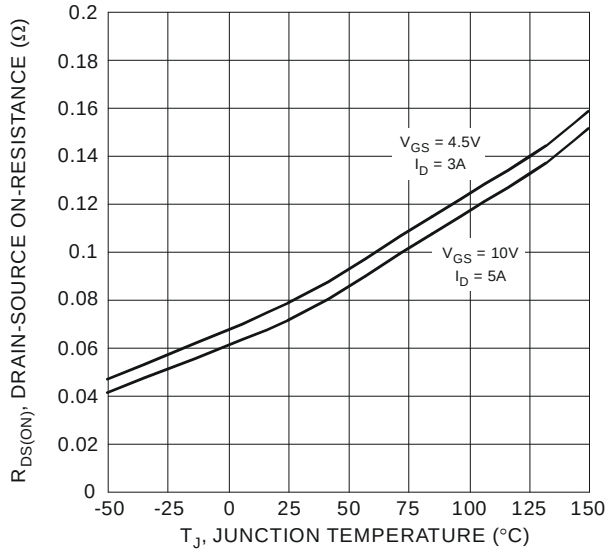
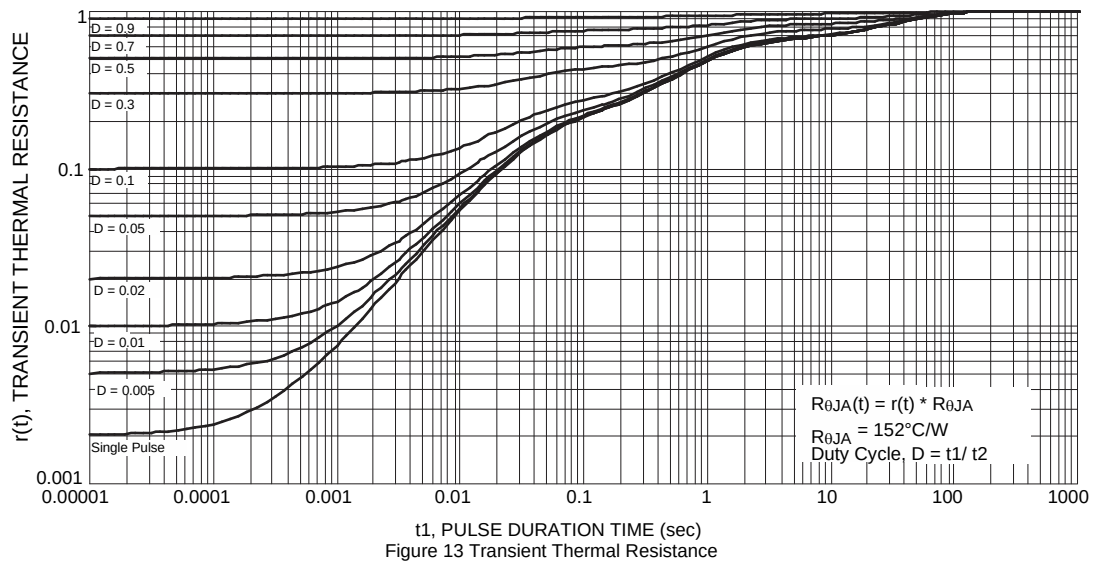


Figure 6 On-Resistance Variation with Temperature

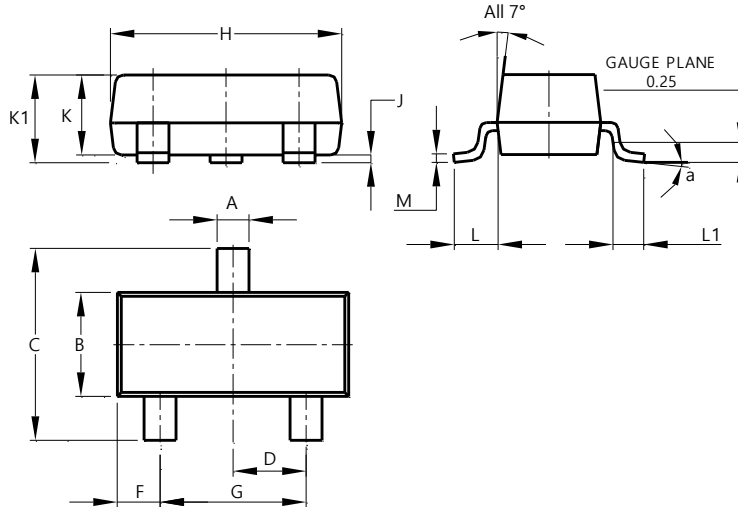




Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

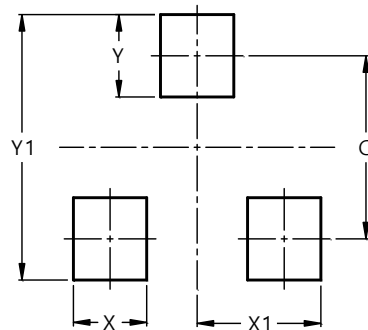


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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